300-Watt C- & X-Band Amplifier Salient Characteristics

Electrical Characteristics

Amplification Type:
GaN Pulsed
Frequency Range:
5.5GHz – 10.5GHz min bandwidth
Input/Output Impedance:
50 ohms
Input Power:
0dBm typical (33dBm max) (this is flexible)
Output Power:
PSAT > 55dBm (300W)
Duty Cycle:
15% max
PAE:
At Psat = 18% typical (15% min) (this is flexible)
Gain at Psat:
> 55dB typical (this is flexible)
Gain Flatness (at 0dBm Input):
< +/-3dB (this is flexible)
VSWR:
< 3:1
Biases:
VD < or = 40v DC
Max DC Power:
< 1500W
Input/Output Return Loss:
< 15dB
Blanking Type:
RF Gating
Blanking Logic:
TTL 3v to 5v
Blanking Response Time:
< 2uS RF on/off

Mechanical specifications

Package Type:
Connectorized Module
Dimensions:
12L x 10W x 5D inch max
305L x 254W x 127 mm max (these dimensions are flexible)
Connector Types:
Input: SMA female
Output: SMA, TNC or N-Type female

Environmental Specifications

Operating Temperature Range:
-20C to +65C min
Storage temperature:
-40C to +85C min
Cooling Type:
Forced Air Over External Heatsink